## NSN 5962-01-364-2689

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| Maximum Power Dissipation Rating:  |
|--|
| 1.0 watts  |
| Operating Tempurature Range:   |
| -55.0/+125.0 degrees celsius   |
| Storage Tempurature Range:   |
| -65.0/+150.0 degrees celsius   |
| Features Provided:   |
| Burn in and electrostatic sensitive and monolithic and programmed and w/register output                            |
| Inclosure Material:  |
| Ceramic  |
| Inclosure Configuration:   |
| Dual-in-line   |
| Output Logic Form:   |
| Complementary-metal oxide-semiconductor logic  |
| Input Circuit Pattern:   |
| 14 input   |
| Case Outline Source And Designator:  |
| D-9 mil-m-38510  |
| Terminal Surface Treatment:  |
| Solder   |
| Voltage Rating And Type Per Characteristic:  |
| 5.0 volts applied  |
| Memory Device Type:  |
| Prom   |
| Test Data Document:  |
| 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). |
| Terminal Type And Quantity:  |
| 24 printed circuit   |
| Shelf Life:  |
| N/a  |
| Unit Of Measure:   |
|  |
| Demilitarization:  |
| Yes - demil/mli  |
| Fiig:  |
| A458a0   |
|  |